IS61C512

64K x 8 HIGH-SPEED CMOS STATIC RAM

FEATURES

- Pin compatible with 128K x 8 devices
- High-speed access time: 15, 20, 25, 35 ns
- Low active power: 500 mW (typical)
- Low standby power
  — 250 μW (typical) CMOS standby
- Output Enable ($\overline{OE}$) and two Chip Enable ($\overline{CE1}$ and CE2) inputs for ease in applications
- Fully static operation: no clock or refresh required
- TTL compatible inputs and outputs
- Single 5V (±10%) power supply

DESCRIPTION

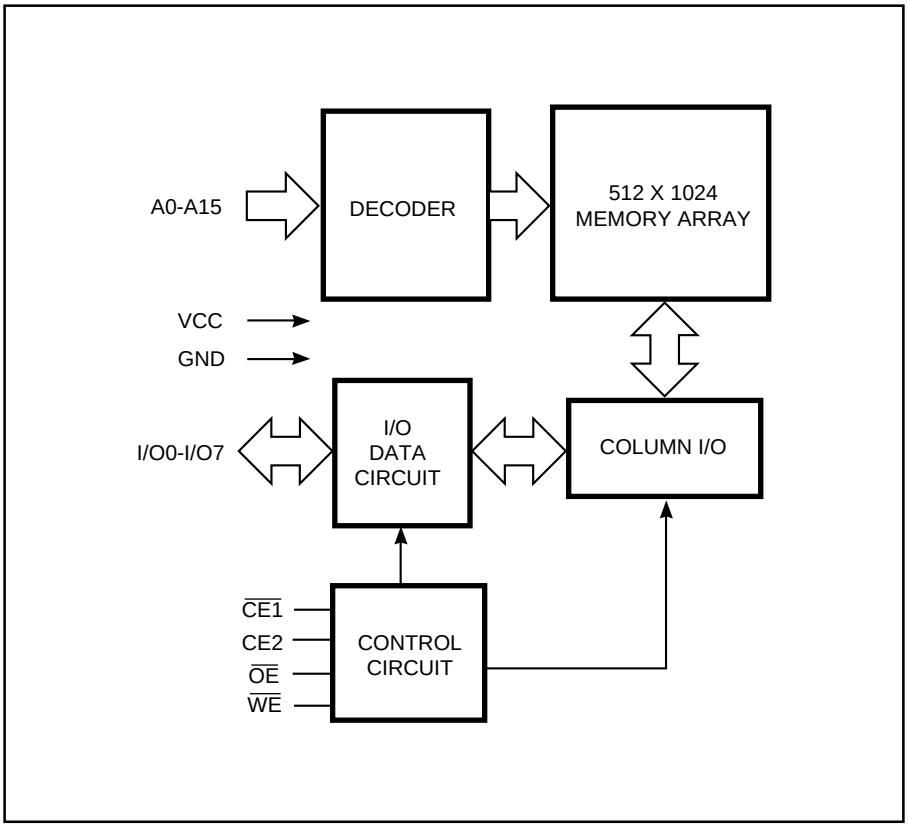
The *ICSI* IS61C512 is a very high-speed, low power, 65,536 word by 8-bit CMOS static RAMs. They are fabricated using *ICSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields higher performance and low power consumption devices.

When $\overline{CE1}$ is HIGH or CE2 is LOW (deselected), the device assumes a standby mode at which the power dissipation can be reduced down to 1 mW (typical) with CMOS input levels.

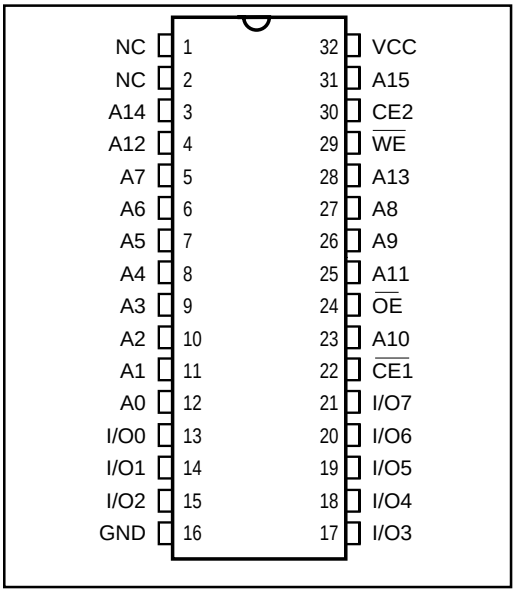
Easy memory expansion is provided by using two Chip Enable inputs, $\overline{CE1}$ and CE2. The active LOW Write Enable ($\overline{WE}$) controls both writing and reading of the memory.

The IS61C512 is available in 32-pin 300mil DIP, SOJ and 8*20mm TSOP-1 packages.

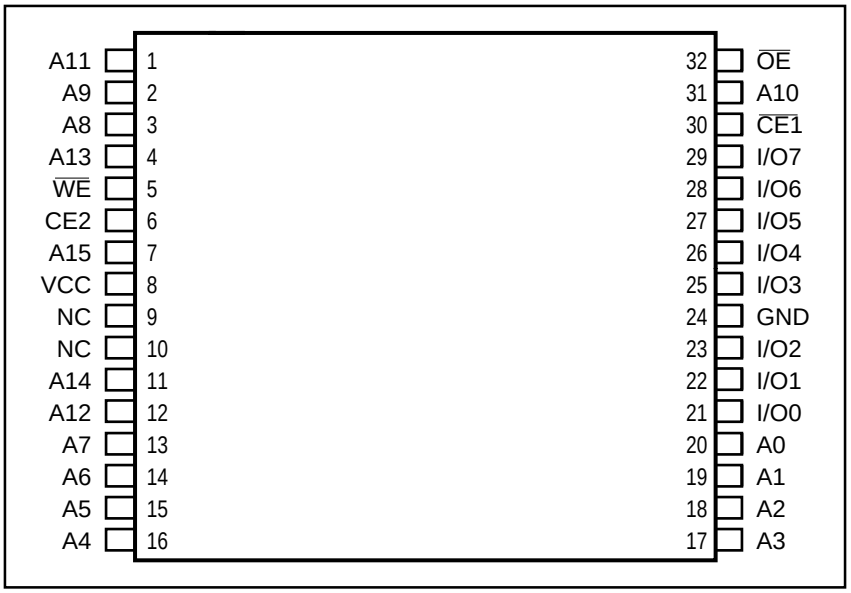
FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION
32-Pin DIP and SOJ



PIN CONFIGURATION
32-Pin TSOP-1



PIN DESCRIPTIONS

A0-A15	Address Inputs
$\overline{CE1}$	Chip Enable 1 Input
CE2	Chip Enable 2 Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Input/Output
Vcc	Power
GND	Ground

TRUTH TABLE

Mode	$\overline{WE}$	$\overline{CE1}$	CE2	$\overline{OE}$	I/O Operation	Vcc Current
Not Selected	X	H	X	X	High-Z	I_{SB1}, I_{SB2}
(Power-down)	X	X	L	X	High-Z	I_{SB1}, I_{SB2}
Output Disabled	H	L	H	H	High-Z	I_{CC1}, I_{CC2}
Read	H	L	H	L	D_{OUT}	I_{CC1}, I_{CC2}
Write	L	L	H	X	D_{IN}	I_{CC1}, I_{CC2}

ABSOLUTE MAXIMUM RATINGS[1]

Symbol	Parameter	Value	Unit
V_{TERM}	Terminal Voltage with Respect to GND	–0.5 to +7.0	V
T_{BIAS}	Temperature Under Bias	–10 to +85	°C
T_{STG}	Storage Temperature	–65 to +150	°C
P_T	Power Dissipation	1.5	W
I_{OUT}	DC Output Current (LOW)	20	mA

Notes:
1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	5V ± 10%
Industrial	–40°C to +85°C	5V ± 10%

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA	2.4	—	V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA	—	0.4	V
V_{IH}	Input HIGH Voltage		2.2	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage[1]		–0.3	0.8	V
I_{LI}	Input Leakage	GND ≤ V_{IN} ≤ V_{CC}	–2	2	µA
I_{LO}	Output Leakage	GND ≤ V_{OUT} ≤ V_{CC}, Outputs Disabled	–2	2	µA

Notes:
1. V_{IL} = –3.0V for pulse width less than 10 ns.

POWER SUPPLY CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	Test Conditions		-15 ns Min.	-15 ns Max.	-20 ns Min.	-20 ns Max.	-25 ns Min.	-25 ns Max.	-35 ns Min.	-35 ns Max.	Unit
I_{CC1}	Vcc Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = 0	Com.	—	70	—	70	—	70	—	70	mA
			Ind.	—	—	—	90	—	90	—	90	
I_{CC2}	Vcc Dynamic Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA, f = f_{MAX}	Com.	—	125	—	115	—	105	—	90	mA
			Ind.	—	—	—	135	—	125	—	115	
I_{SB1}	TTL Standby Current (TTL Inputs)	V_{CC} = Max., V_{IN} = V_{IH} or V_{IL} $\overline{CE1}$ ≥ V_{IH} or CE2 ≤ V_{IL}, f = 0	Com.	—	25	—	25	—	25	—	25	mA
			Ind.	—	—	—	30	—	30	—	30	
I_{SB2}	CMOS Standby Current (CMOS Inputs)	V_{CC} = Max., $\overline{CE1}$ ≥ V_{CC} – 0.2V, CE2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V, or V_{IN} ≤ 0.2V, f = 0	Com.	—	750	—	750	—	750	—	750	µA
			Ind.	—	—	—	1	—	1	—	1	mA

Notes:
1. At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.

CAPACITANCE[1,2]

Symbol	Parameter	Conditions	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	5	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	7	pF

Notes:
1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, Vcc = 5.0V.

READ CYCLE SWITCHING CHARACTERISTICS[1] (Over Operating Range)

Symbol	Parameter	-15 ns Min.	-15 ns Max.	-20 ns Min.	-20 ns Max.	-25 ns Min.	-25 ns Max.	-35 ns Min.	-35 ns Max.	Unit
t_{RC}	Read Cycle Time	15	—	20	—	25	—	35	—	ns
t_{AA}	Address Access Time	—	15	—	20	—	25	—	35	ns
t_{OHA}	Output Hold Time	3	—	3	—	3	—	3	—	ns
t_{ACE1}	$\overline{CE1}$ Access Time	—	15	—	20	—	25	—	35	ns
t_{ACE2}	CE2 Access Time	—	15	—	20	—	25	—	35	ns
t_{DOE}	$\overline{OE}$ Access Time	—	7	—	8	—	9	—	12	ns
t_{LZOE}[2]	$\overline{OE}$ to Low-Z Output	0	—	0	—	0	—	0	—	ns
t_{HZOE}[2]	$\overline{OE}$ to High-Z Output	0	6	0	9	0	10	0	12	ns
t_{LZCE1}[2]	$\overline{CE1}$ to Low-Z Output	2	—	3	—	3	—	3	—	ns
t_{LZCE2}[2]	CE2 to Low-Z Output	2	—	3	—	3	—	3	—	ns
t_{HZCE}[2]	$\overline{CE1}$ or CE2 to High-Z Output	0	8	0	9	0	10	0	12	ns
t_{PU}[3]	$\overline{CE1}$ or CE2 to Power-Up	0	—	0	—	0	—	0	—	ns
t_{PD}[3]	$\overline{CE1}$ or CE2 to Power-Down	—	12	—	18	—	20	—	20	ns

Notes:
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	3 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1a and 1b

AC TEST LOADS

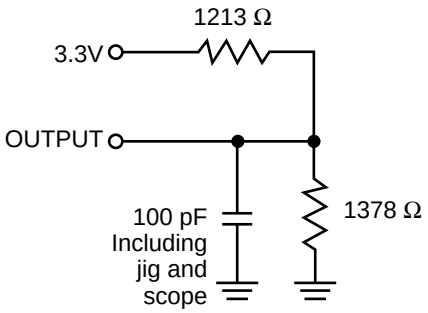


Figure 1a.

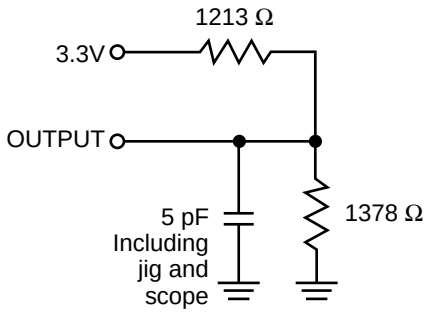
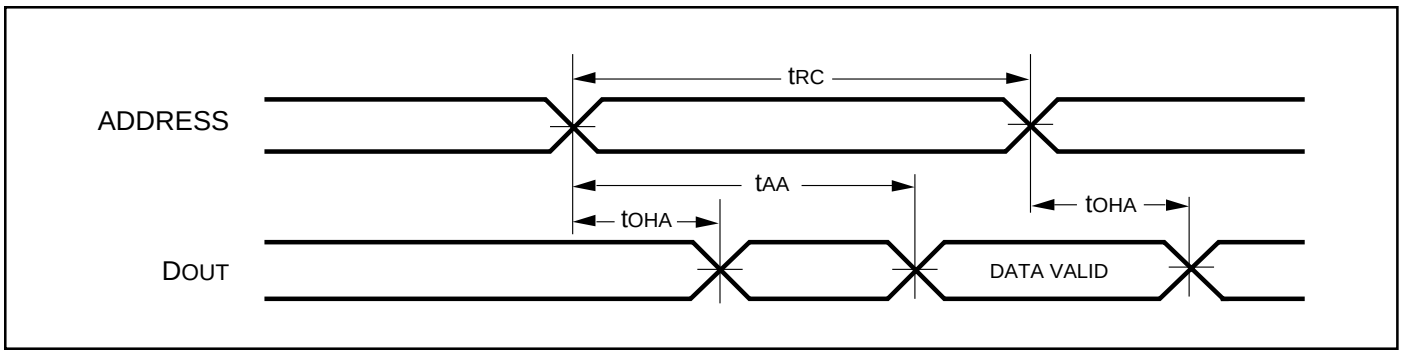


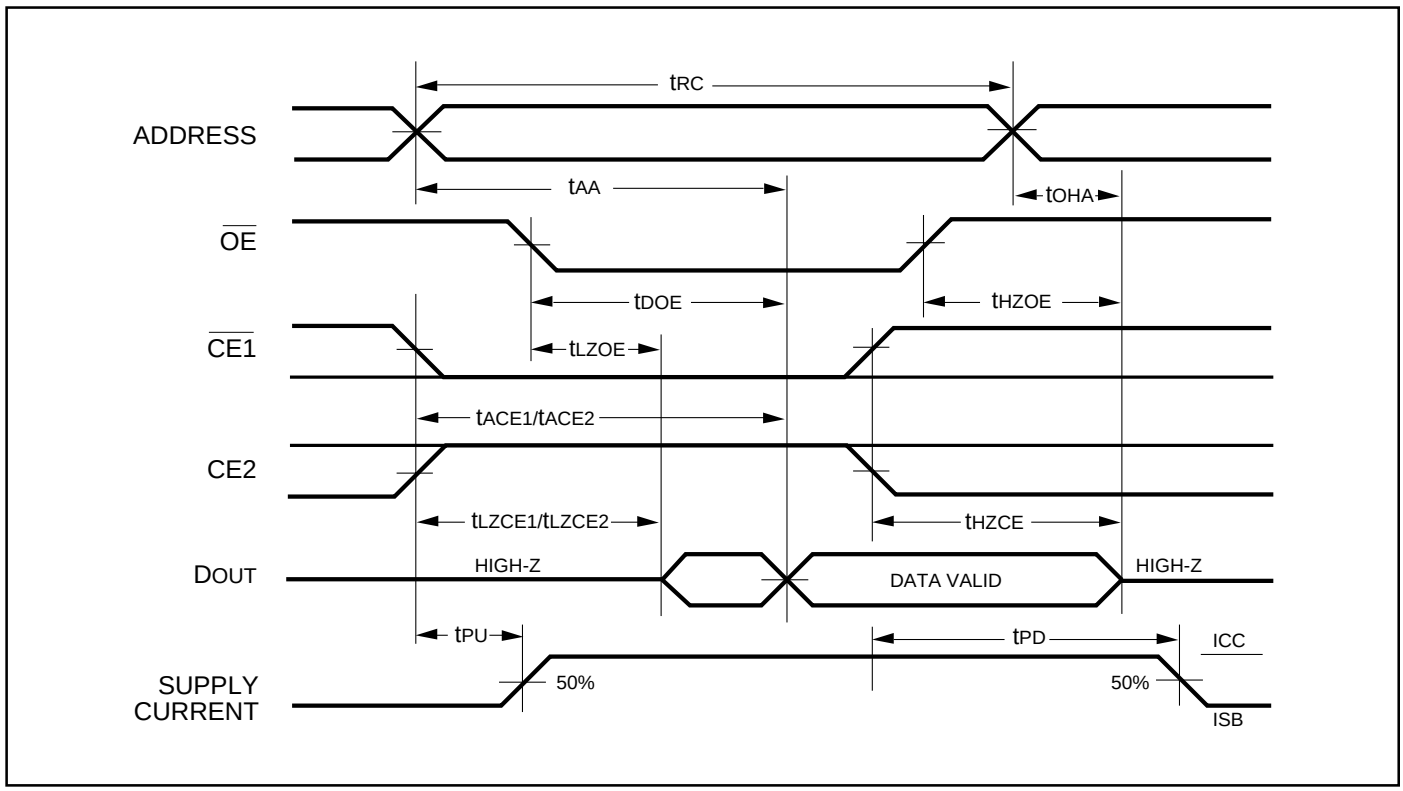
Figure 1b.

AC WAVEFORMS

READ CYCLE NO. 1[1,2]



READ CYCLE NO. 2[1,3]



Notes:
1. $\overline{WE}$ is HIGH for a Read Cycle.
2. The device is continuously selected. $\overline{OE}$, $\overline{CE1}$ = V_{IL}, CE2 = V_{IH}.
3. Address is valid prior to or coincident with $\overline{CE1}$ LOW and CE2 HIGH transitions.

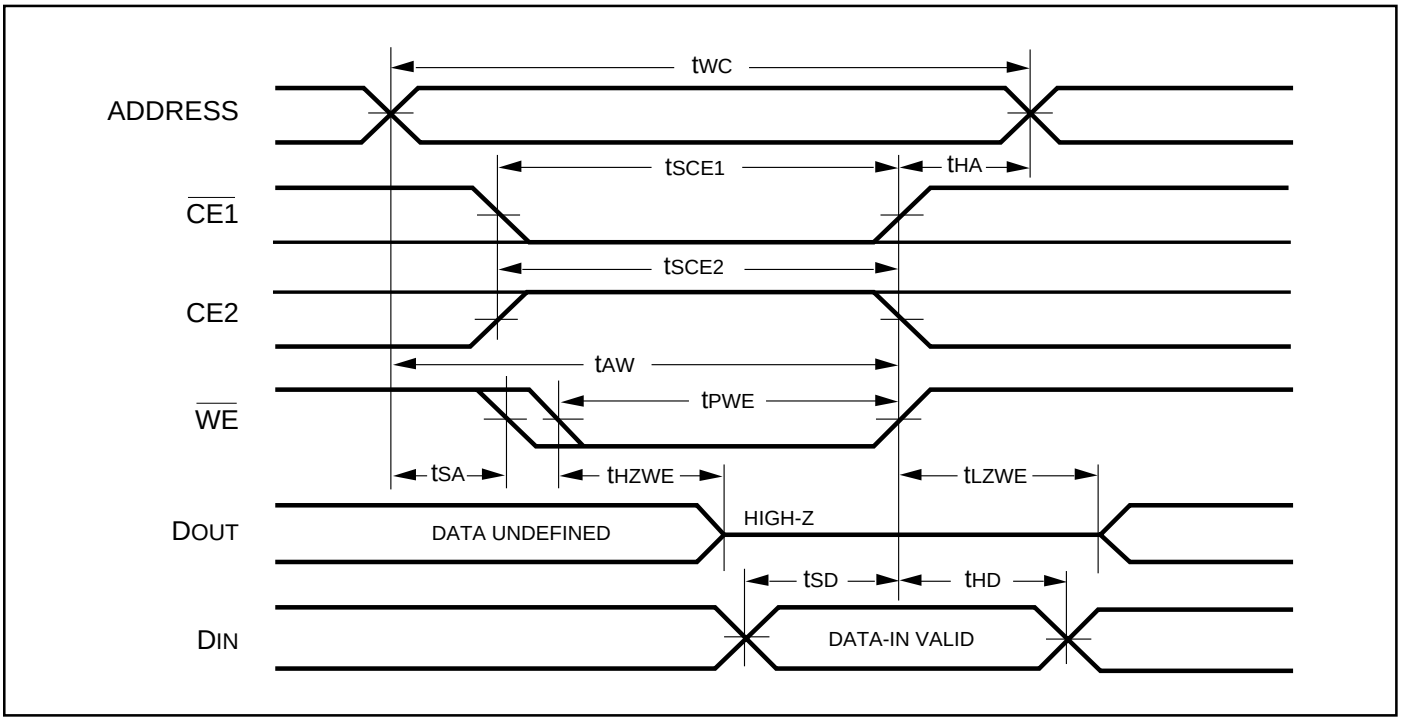
WRITE CYCLE SWITCHING CHARACTERISTICS[1,3] (Over Operating Range)

Symbol	Parameter	-15 ns Min.	-15 ns Max.	-20 ns Min.	-20 ns Max.	-25 ns Min.	-25 ns Max.	-35 ns Min.	-35 ns Max.	Unit
t_{WC}	Write Cycle Time	15	—	20	—	25	—	35	—	ns
t_{SCE1}	$\overline{CE1}$ to Write End	12	—	15	—	20	—	30	—	ns
t_{SCE2}	CE2 to Write End	12	—	15	—	20	—	30	—	ns
t_{AW}	Address Setup Time to Write End	12	—	15	—	20	—	30	—	ns
t_{HA}	Address Hold from Write End	0	—	0	—	0	—	0	—	ns
t_{SA}	Address Setup Time	0	—	0	—	0	—	0	—	ns
t_{PWE}[4]	$\overline{WE}$ Pulse Width	10	—	12	—	15	—	20	—	ns
t_{SD}	Data Setup to Write End	8	—	10	—	12	—	15	—	ns
t_{HD}	Data Hold from Write End	0	—	0	—	0	—	0	—	ns
t_{HZWE}[2]	$\overline{WE}$ LOW to High-Z Output	—	7	—	10	—	12	—	8	ns
t_{LZWE}[2]	$\overline{WE}$ HIGH to Low-Z Output	2	—	2	—	2	—	2	—	ns

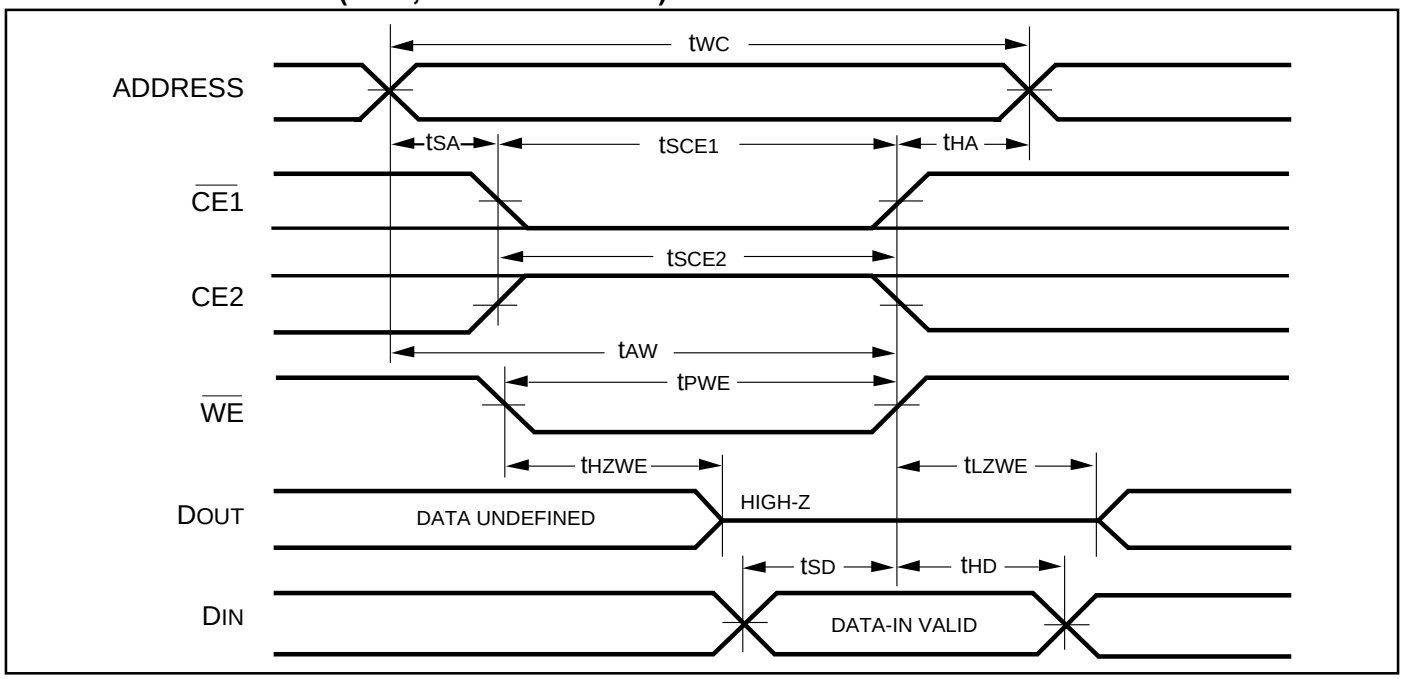
Notes:
1. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1a.
2. Tested with the load in Figure 1b. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of $\overline{CE1}$ LOW, CE2 HIGH and $\overline{WE}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
4. Tested with $\overline{OE}$ HIGH.

AC WAVEFORMS

WRITE CYCLE NO. 1 ($\overline{WE}$ Controlled)[1,2]



WRITE CYCLE NO. 2 ($\overline{CE1}$, CE2 Controlled)[1,2]



Notes:
1. The internal write time is defined by the overlap of $\overline{CE1}$ LOW, CE2 HIGH and $\overline{WE}$ LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.
2. I/O will assume the High-Z state if $\overline{OE}$ = HIGH.

ORDERING INFORMATION: IS61C512
Commercial Range: 0°C to + 70°C

Speed (ns)	Order Part No.	Package
15	IS61C512-15J	300mil SOJ
15	IS61C512-15N	300mil DIP
15	IS61C512-15T	8*20mm TSOP-1
20	IS61C512-20J	300mil SOJ
20	IS61C512-20N	300mil DIP
20	IS61C512-20T	8*20mm TSOP-1
25	IS61C512-25J	300mil SOJ
25	IS61C512-25N	300mil DIP
25	IS61C512-25T	8*20mm TSOP-1
35	IS61C512-35J	300mil SOJ
35	IS61C512-35N	300mil DIP
35	IS61C512-35T	8*20mm TSOP-1

ORDERING INFORMATION: IS61C512
Industrial Range: –40°C to + 85°C

Speed (ns)	Order Part No.	Package
15	IS61C512-15JI	300mil SOJ
15	IS61C512-15NI	300mil DIP
15	IS61C512-15TI	8*20mm TSOP-1
20	IS61C512-20JI	300mil SOJ
20	IS61C512-20NI	300mil DIP
20	IS61C512-20TI	8*20mm TSOP-1
25	IS61C512-25JI	300mil SOJ
25	IS61C512-25NI	300mil DIP
25	IS61C512-25TI	8*20mm TSOP-1
35	IS61C512-35JI	300mil SOJ
35	IS61C512-35NI	300mil DIP
35	IS61C512-35TI	8*20mm TSOP-1

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